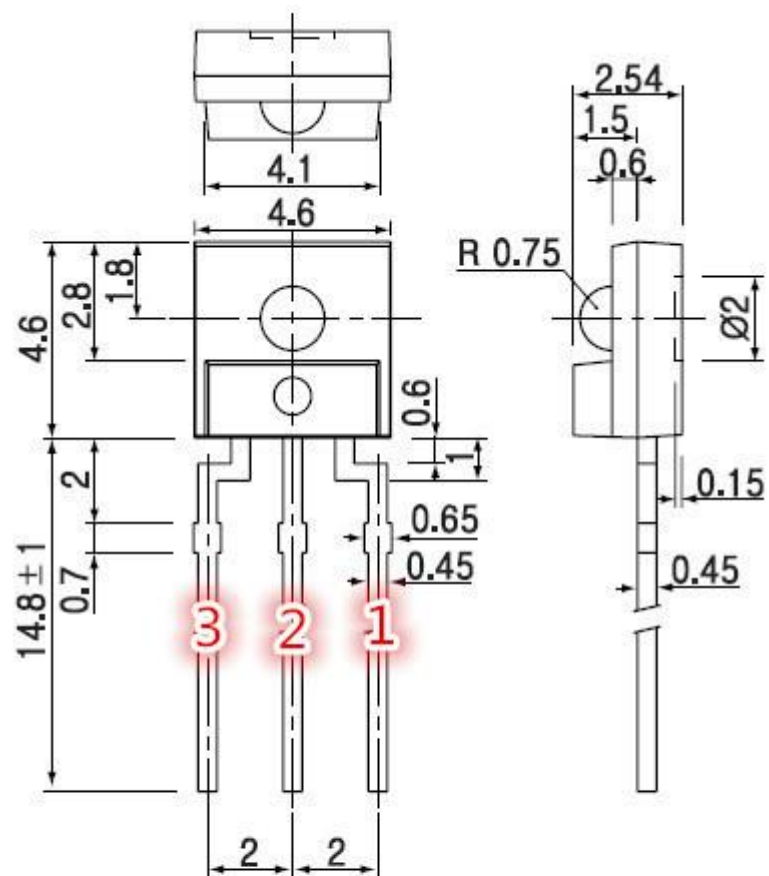
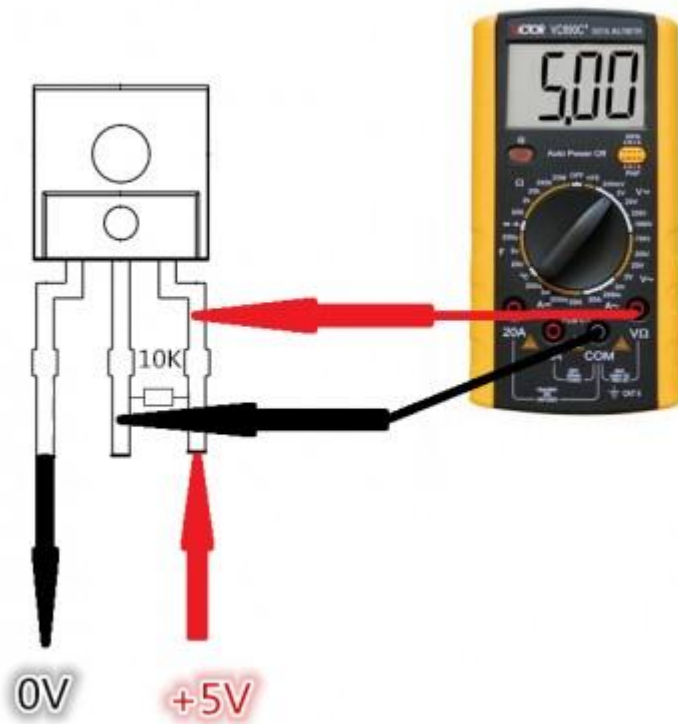
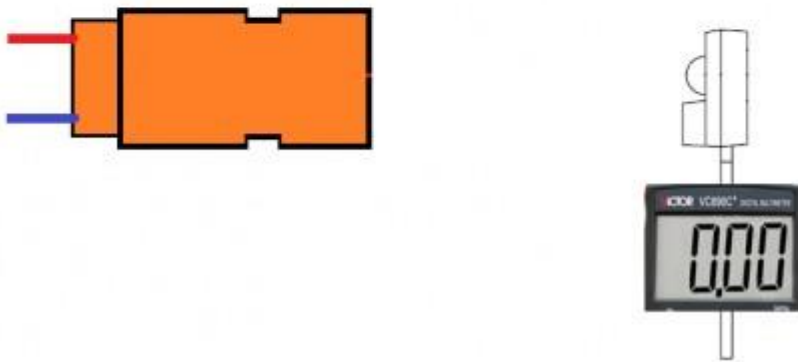
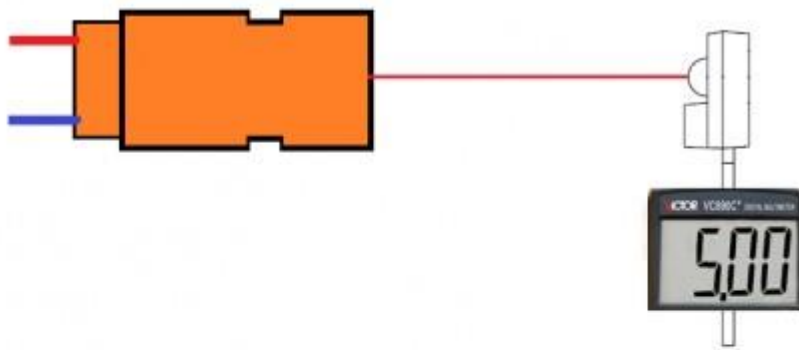




MAXIMUM RATINGS

(Ta=25°C)

Item	Symbol	Rating	Unit
Supply voltage	V _{CC}	17	V
Low level output current	I _{OL}	30	mA
Output transistor power dissipation	P _o	200	mW
Operating temp.	T _{opr.}	-25~+85	°C
Storage temp.	T _{stg.}	-40~+100	°C
Soldering temp.*1	T _{sol.}	260	°C

*1. For MAX, 5 seconds at the position of 2 mm from the resin edge.

ELECTRO-OPTICAL CHARACTERISTICS

(V_{CC}=5V, Ta=25°C)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Supply voltage	V _{CC}		4.5		17	V
High level supply current	I _{CCH}	E _V =0lx		3	6	mA
Low level supply current	I _{CCL}	E _V =100lx		3	6	mA
High level output voltage	V _{OH}	E _V =100lx, E=10K Ω , V _{OUT} =5V	4.5			V
Low level output voltage	V _{OL}	E _V =100lx, I _L =16mA			0.4	V
L→H Threshold illuminance	E _{VLH}		10	25		lx
H→L Threshold illuminance	E _{VHL}			30	80	lx
Hysteresis	E _{VHL} /E _{VLH}	R _L =280 Ω	0.5	0.8	0.95	—
Peak wavelength	λ P			900		nm
Switching speed	L→H propagation time	E _V =100lx, R=280 Ω		3	9	μ sec.
	H→L propagation time			2	6	μ sec.
	Rise time			0.1	0.5	μ sec.
	Fall time			0.05	0.5	μ sec.